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<input type="checkbox"/>	9.	Quantum-size effects in hafnium-oxide resistive switching By: Long, Shibing; Lian, Xiaojuan; Cagli, Carlo; et al. APPLIED PHYSICS LETTERS Volume: 102 Issue: 18 Article Number: 183505 Published: MAY 6 2013	8	25	17	20	0	70	14.00
<input type="checkbox"/>	10.	Power-law voltage acceleration: A key element for ultra-thin gate oxide reliability By: Wu, EY; Sune, J MICROELECTRONICS RELIABILITY Volume: 45 Issue: 12 Pages: 1809-1834 Published: DEC 2005	12	3	2	5	0	70	5.38
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